



[ThB1] Atomic Scale Etching

Session Date	November 13 (Thu.), 2025
Session Time	09:00–10:40
Session Room	Room B (Grand Ballroom 1, 2F)
Session Chair	Prof. Thi-Thuy-Nga Nguyen (Nagoya Univ., Japan)

[ThB1-1] [Invited]

09:00–09:30

Challenges and Approaches of HARC Patterning for AI Memory Devices

Yeonghun Han (SK hynix Inc., Korea)

[ThB1-2] [Invited]

09:30–10:00

Conversion-Free Atomic Layer Etching (ALE) of ZnO: Effect of Precursor on the ALE Process

Taewook Nam (Sejong Univ., Korea)

[ThB1-3] [Invited]

10:00–10:25

Ab Initio Analysis of Atomistic Diffusion of Halogen Species at the Etching Front

Sangheon Lee (Ewha Womans Univ., Korea)

[ThB1-4]

10:25–10:40

Investigation of Wafer Edge Tilting in Capacitively Coupled Plasmas via IEADF-Driven Monte Carlo Feature-Scale Simulation

Sanghyun Jo (Hanyang Univ., Korea), Kyoung-Ho Kim (Korea Polytechnics, Korea), and Ho Jun Kim (Hanyang Univ., Korea)